

BUK7M22-80E

N-channel 80 V, 22 mΩ standard level MOSFET in LFPAK33

19 September 2016 Product data sheet

1. General description

Standard level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------|--|-----|-----|-----|------|
| V_{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | | - | - | 80 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | | - | - | 37 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 75 | W |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 10 V; I_D = 10 A; T_j = 25 °C; Fig. 11 | | - | 18 | 22 | mΩ |
| Dynamic characteristics | | | | | | | |
| Q_{GD} | gate-drain charge | $I_D = 10 \text{ A}; V_{DS} = 64 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$ | | - | 8 | - | nC |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1 | S | Source | | D I |
| 2 | S | Source | | |
| 3 | S | Source | | G T A |
| 4 | G | Gate | | mbb076 S |
| mb | D | Mounting base; connected to drain | LFPAK33 (SOT1210) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|-----------------------------------------------------------------|---------|--|--|
| | Name | Description | Version | | |
| BUK7M22-80E | LFPAK33 | Plastic single ended surface mounted package (LFPAK33); 8 leads | SOT1210 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK7M22-80E | 72280E |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|-----------------------------------------------------------------|-----|-----|------|
| V_{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | - | 80 | V |
| V_{DGR} | drain-gate voltage | $R_{GS} = 20 \text{ k}\Omega$ | - | 80 | V |
| V _{GS} | gate-source voltage | DC; T _j ≤ 175 °C | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | 75 | W |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | 37 | Α |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u> | - | 26 | Α |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; Fig. 3 | - | 147 | Α |
| T _{stg} | storage temperature | | -55 | 175 | °C |

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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|----------------------------------------------|------------------------------------------------------------------------------------------------------------|--------|-----|------|------|
| Tj | junction temperature | | | -55 | 175 | °C |
| Source-dra | in diode | | ' | ' | | |
| I _S | source current | T _{mb} = 25 °C | | - | 37 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 147 | Α |
| Avalanche | ruggedness | | ' | ' | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 37 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4 | [1][2] | - | 36.9 | mJ |

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.

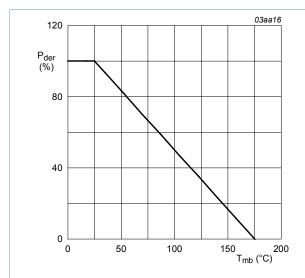


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

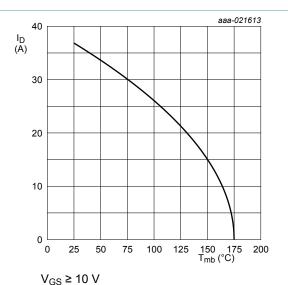
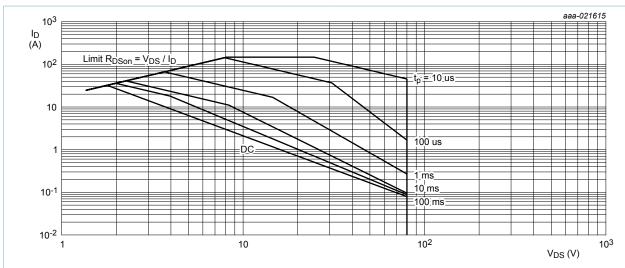


Fig. 2. Continuous drain current as a function of mounting base temperature

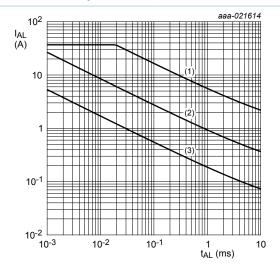
$$I_D = 37A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

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 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

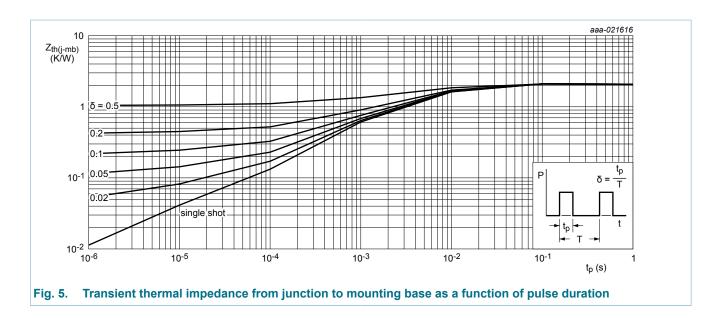
Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------------------------|------------|-----|------|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | - | 1.82 | 2 | K/W |

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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------------|----------------------------------|------------------------------------------------------------------------------|-----|------|-----|------|
| Static charact | eristics | | | | | |
| V _{(BR)DSS} | drain-source | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 80 | - | - | V |
| | breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 72 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10 | 2.4 | 3 | 4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9 | - | - | 4.5 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9 | 1 | - | - | V |
| I _{DSS} | drain leakage current | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 0.01 | 1 | μΑ |
| | | V _{DS} = 80 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 2 | 100 | nA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11 | - | 18 | 22 | mΩ |
| | | V_{GS} = 10 V; I_D = 10 A; T_j = 175 °C; Fig. 12 | - | - | 55 | mΩ |
| Dynamic characteristics | | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 10 A; V _{DS} = 64 V; V _{GS} = 10 V; | - | 23.9 | - | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> | - | 5.7 | - | nC |
| Q_{GD} | gate-drain charge | | - | 8 | - | nC |

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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|------------------------------|------------------------------------------------------------------------------------------------------|---|-----|------|------|------|
| C _{iss} | input capacitance | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_{j} = 25 \text{ °C}; Fig. 15$ | | - | 1235 | 1643 | pF |
| C _{oss} | output capacitance | | | - | 133 | 160 | pF |
| C _{rss} | reverse transfer capacitance | | | - | 78 | 107 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 60 V; R_{L} = 5 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C | | - | 6.4 | - | ns |
| t _r | rise time | | | - | 8.7 | - | ns |
| t _{d(off)} | turn-off delay time | | | - | 17.1 | - | ns |
| t _f | fall time | | | - | 9.2 | - | ns |
| Source-dra | nin diode | 1 | I | | | | |
| V_{SD} | source-drain voltage | $I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$ | | - | 0.83 | 1.2 | V |
| t _{rr} | reverse recovery time | I_S = 10 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C | | - | 25.8 | - | ns |
| Q _r | recovered charge | | | - | 33.5 | - | nC |

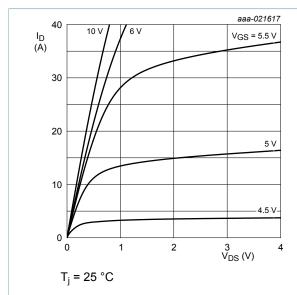


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

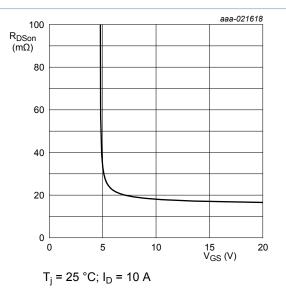


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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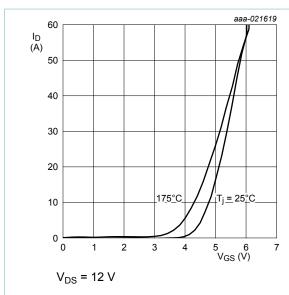


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

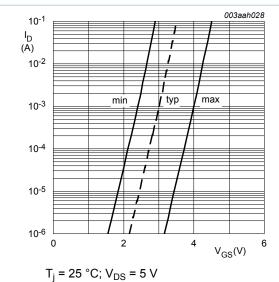


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

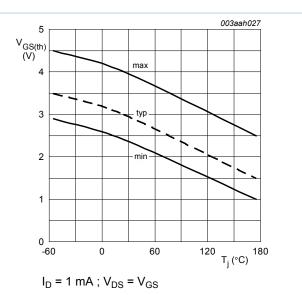


Fig. 9. Gate-source threshold voltage as a function of junction temperature

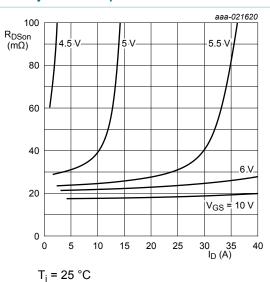


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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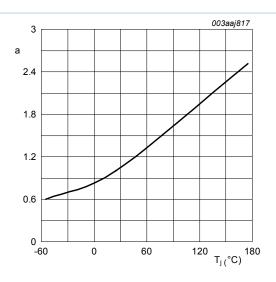


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

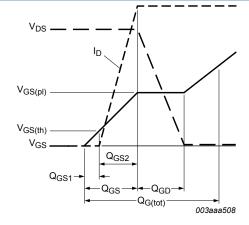


Fig. 14. Gate charge waveform definitions

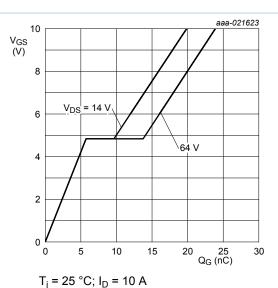


Fig. 13. Gate-source voltage as a function of gate charge; typical values

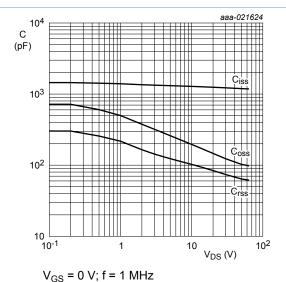
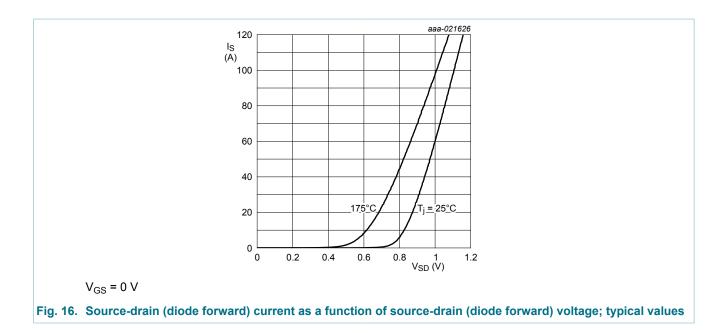


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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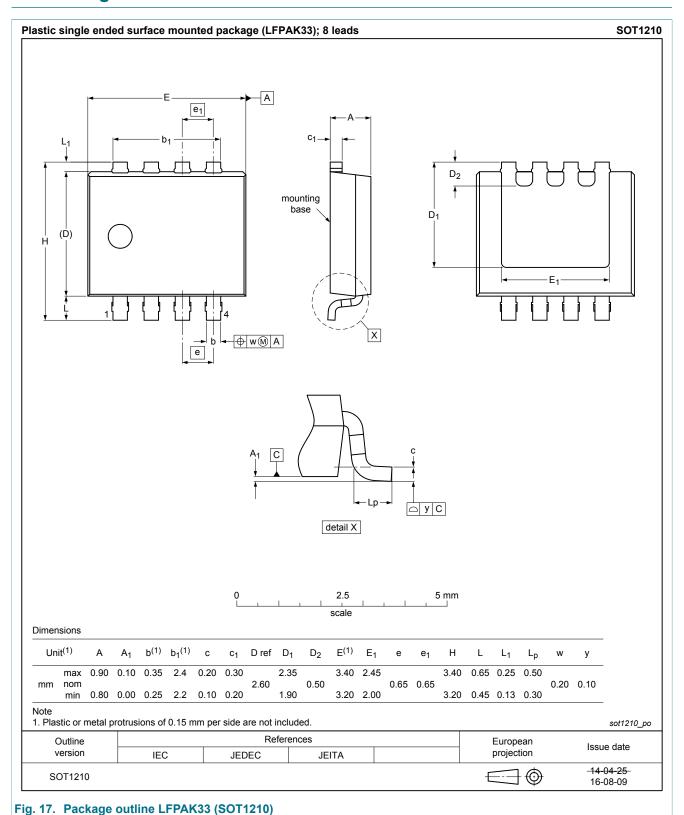
11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

Product data sheet

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12. Package outline



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13. Legal information

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|--------------------------------------|--------------------|---------------------------------------------------------------------------------------|
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| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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